SOP-8

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

N-channel

V_{DS}(V)=40V I_D=15A

$R_{DS(ON)}$@10V<9mΩ

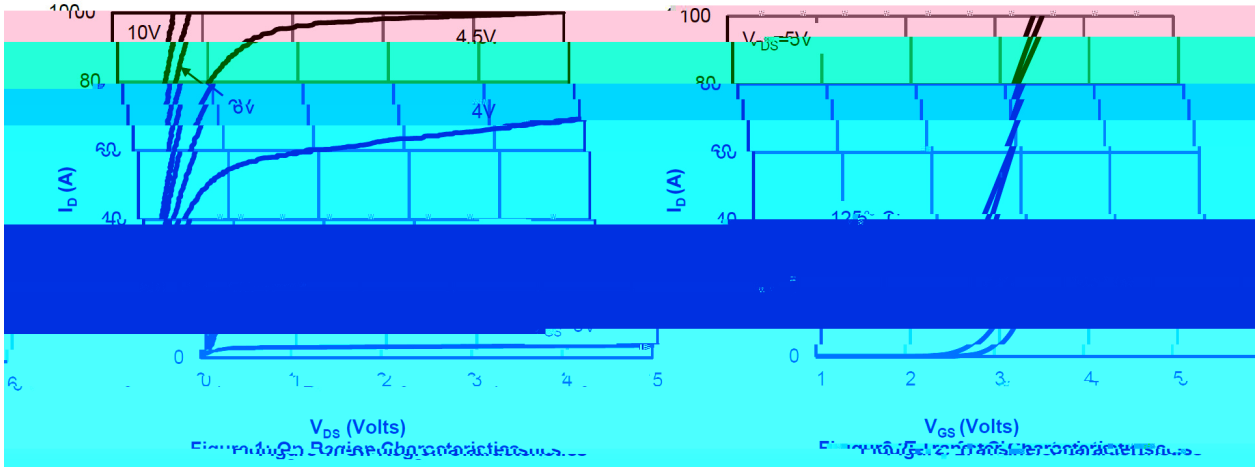
P-channel

V_{DS}(V)=-40V I_D=-11A

DATA SHE

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	40	47		V
Zero Gate Voltage Drain Current BV						

N- / N-CHANNEL Electrical Characteristic Curve



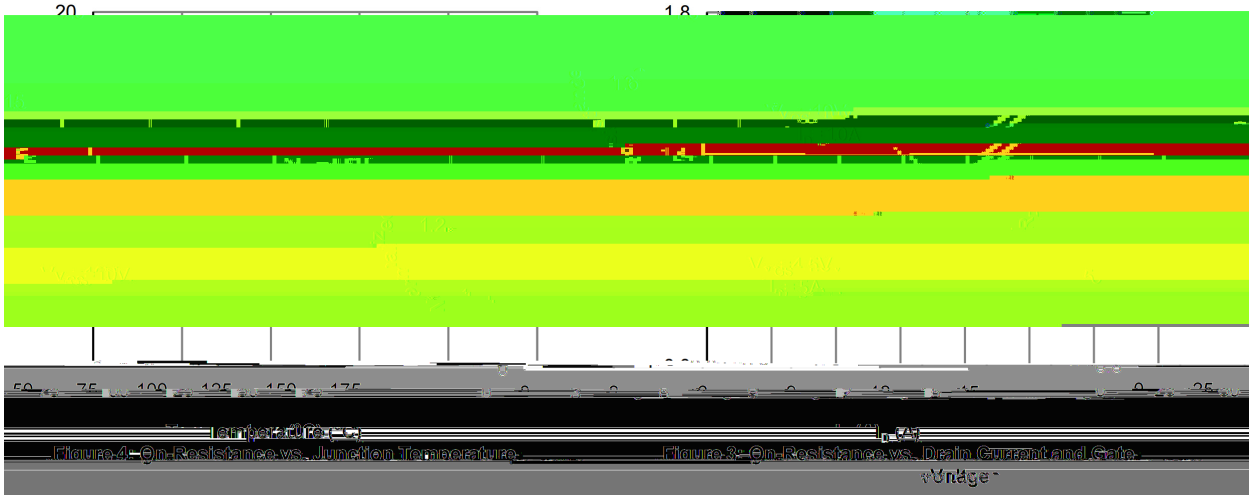
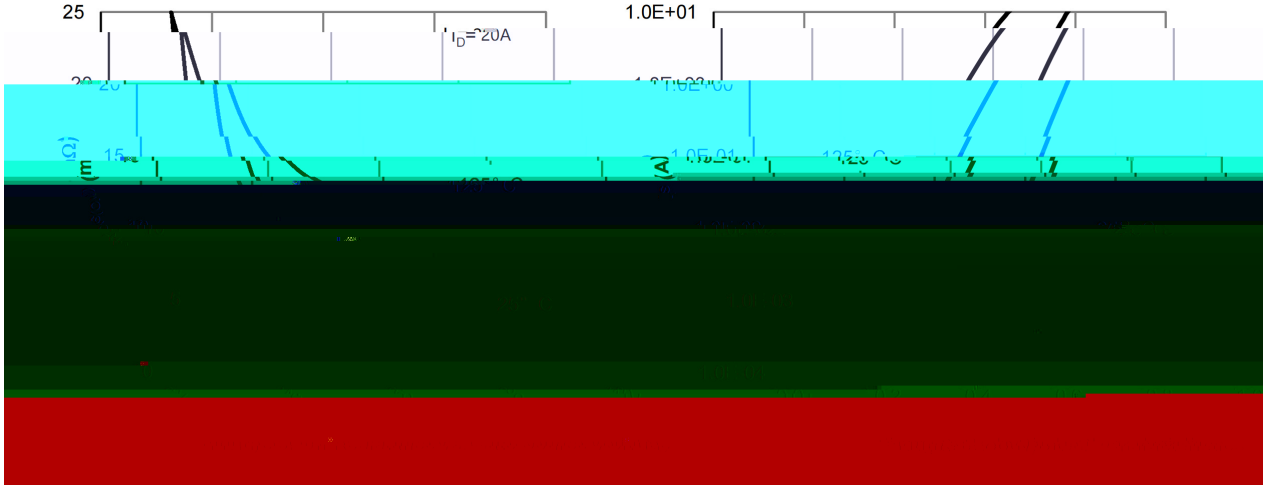


Figure.4 –On-Resistance vs. Junction Temperature

Figure.3 –On-Resistance vs. Drain Current and Gate Voltage



N- / N-CHANNEL Electrical Characteristic Curve

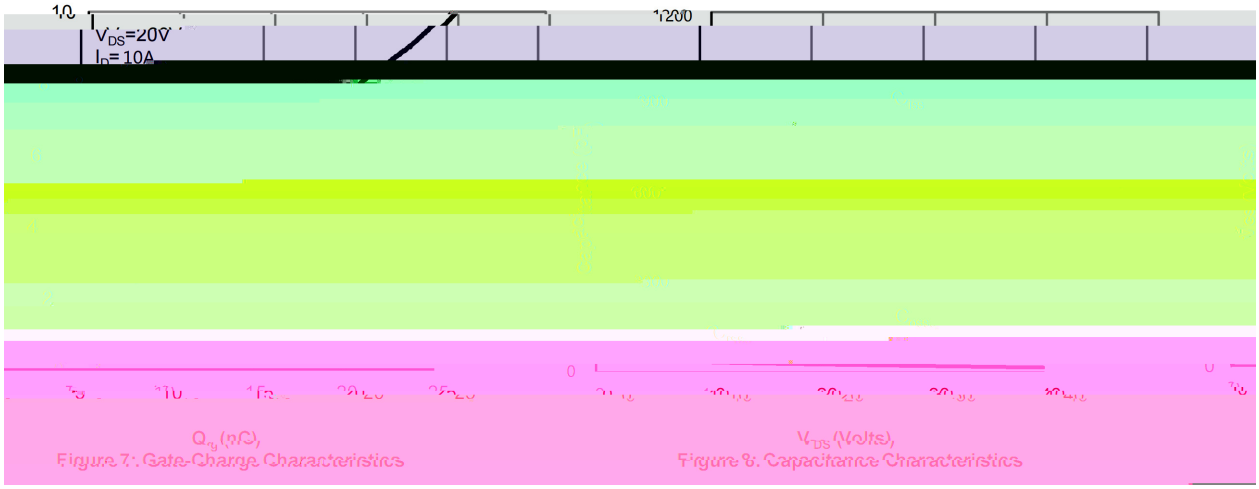
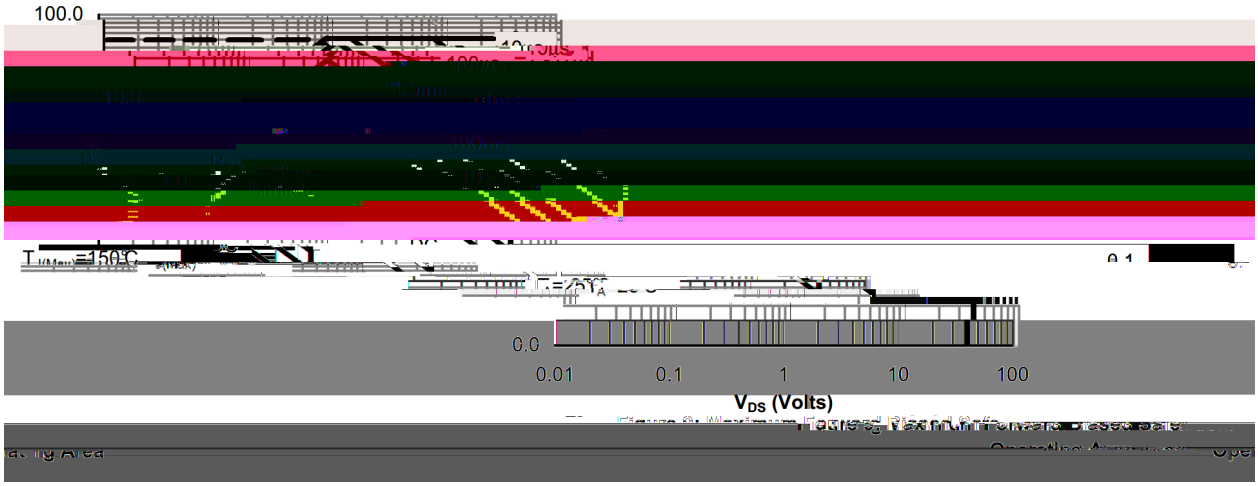
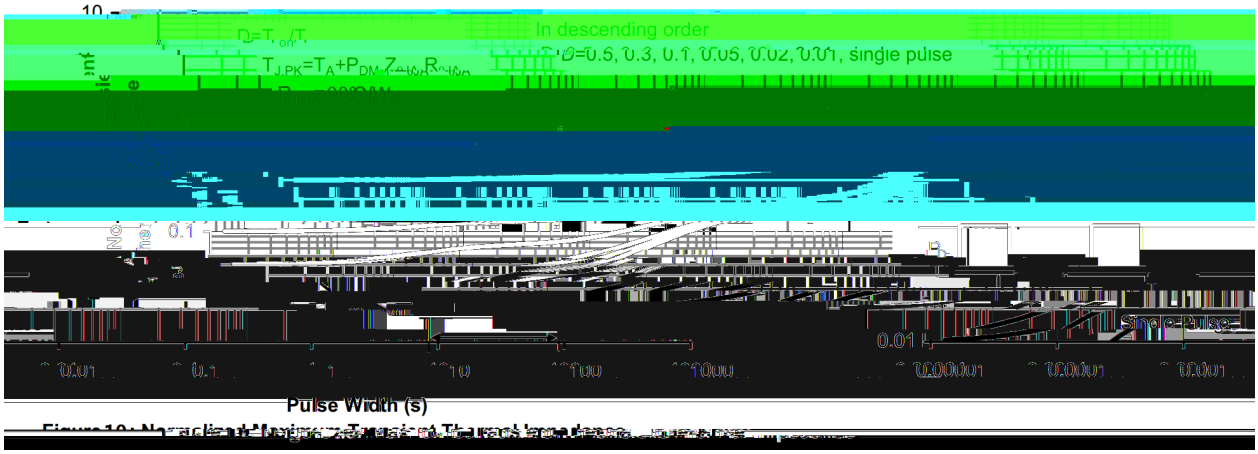


Figure 7: Gate-Charge Characteristics

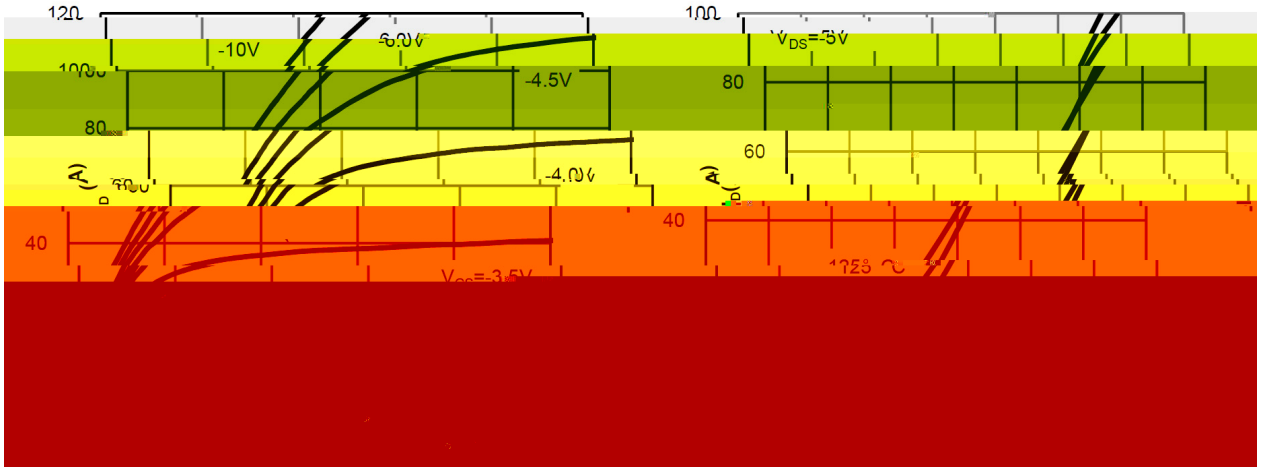
Figure 8: Capacitance Characteristics

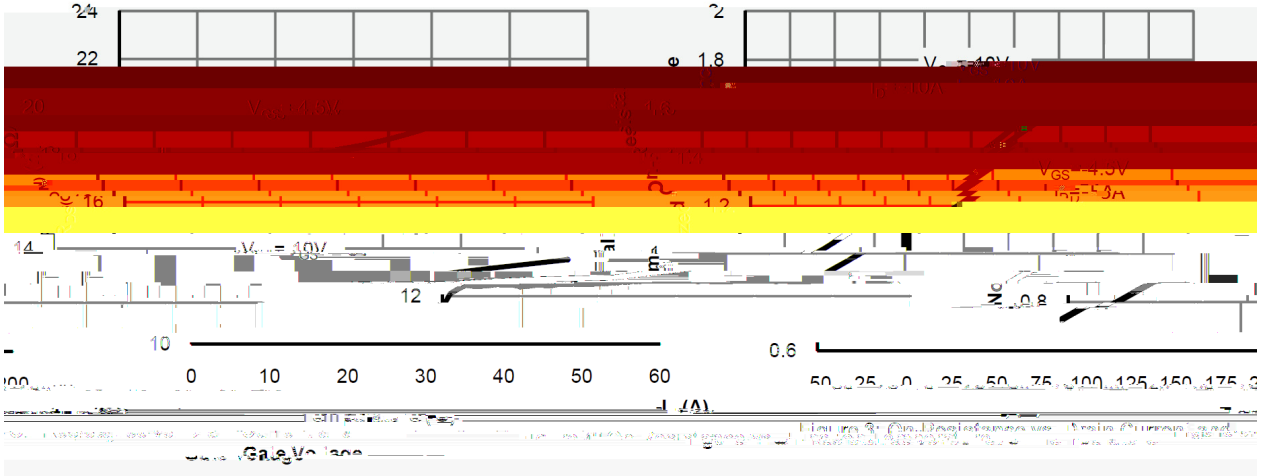




Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-40	-45		V
Zero Gate Voltage Drain Current	I_{DSS}	V				

P- / P-CHANNEL Electrical Characteristic Curve





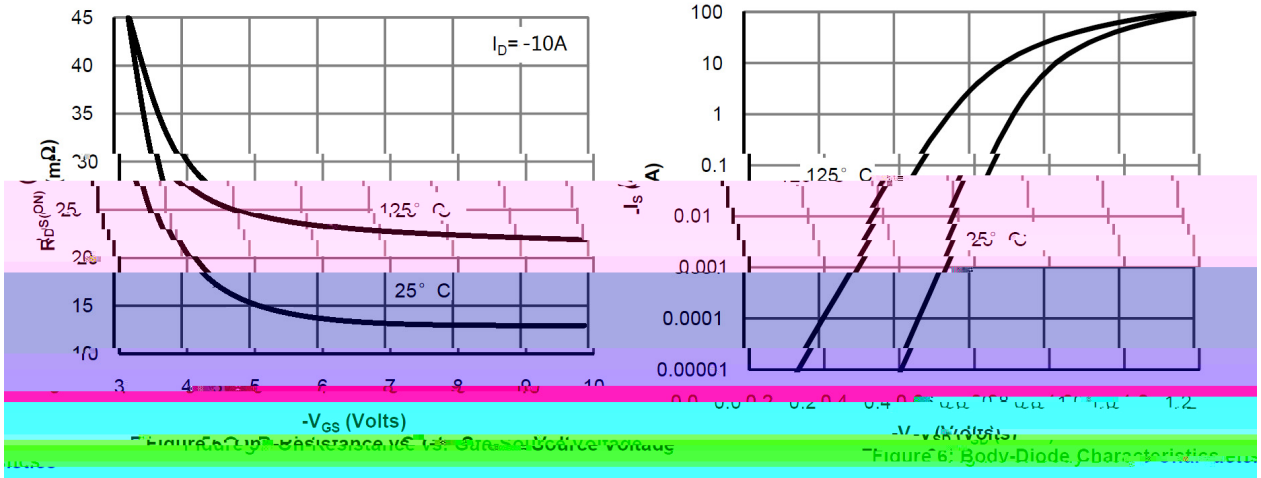
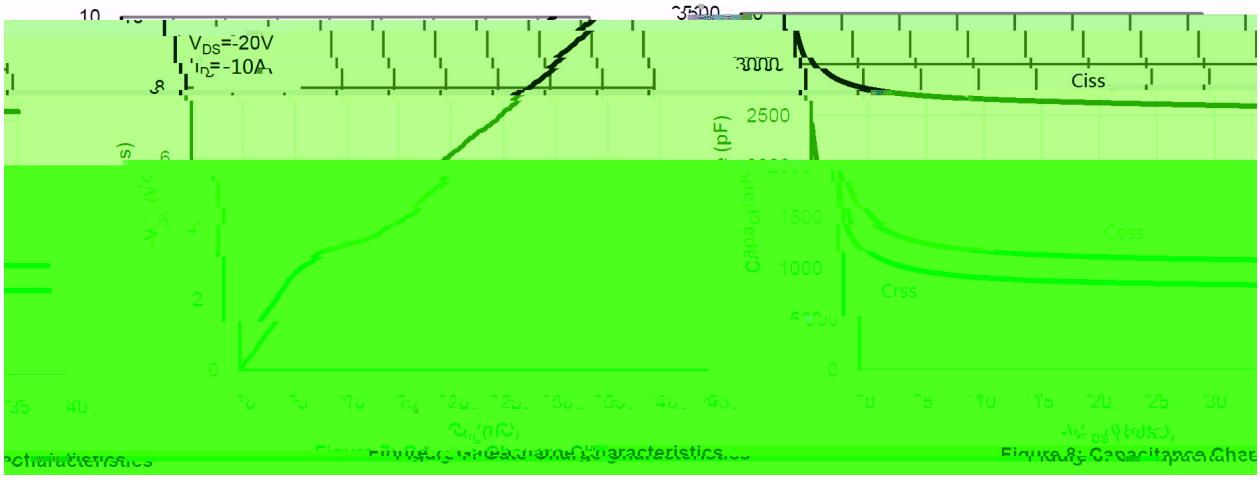
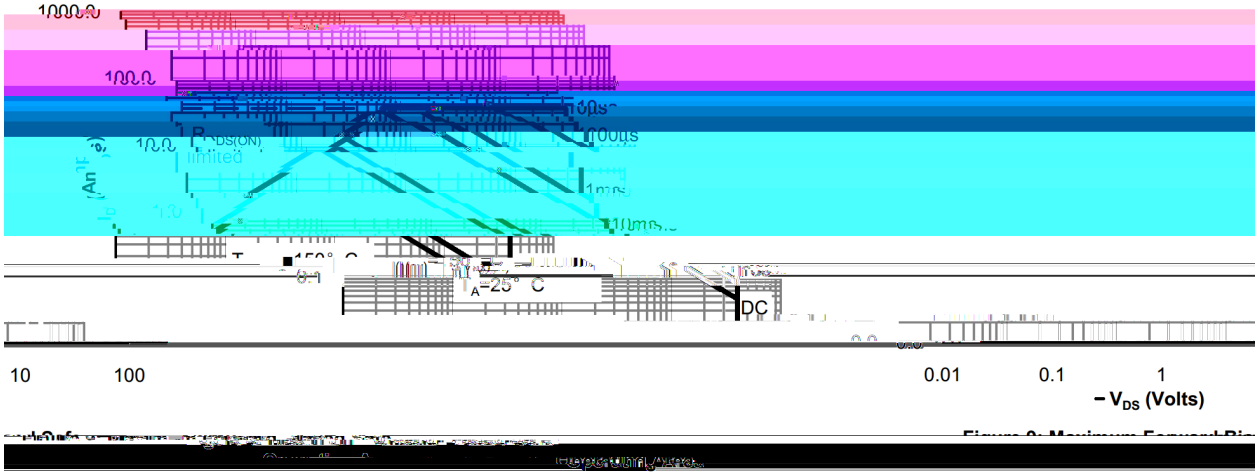


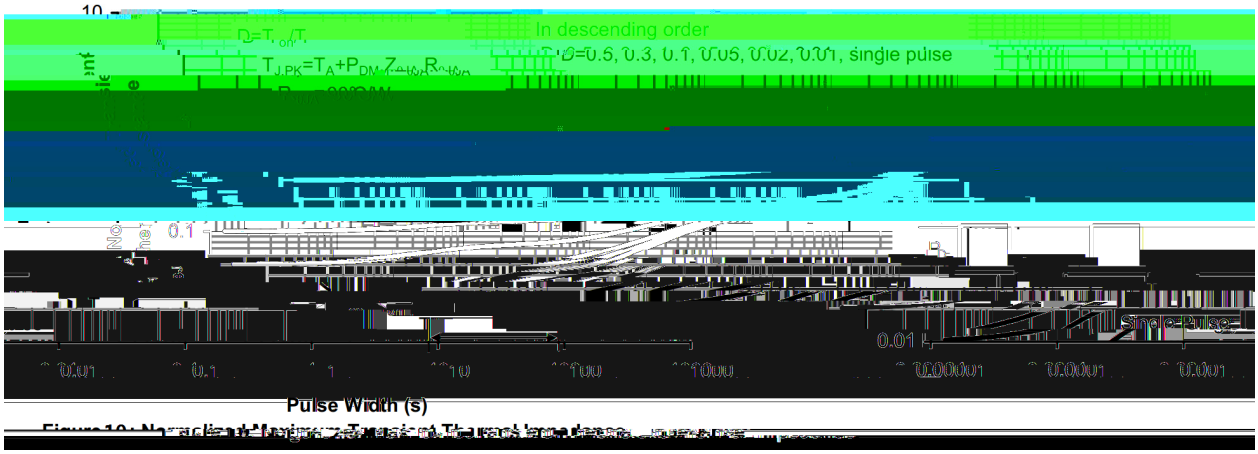
Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

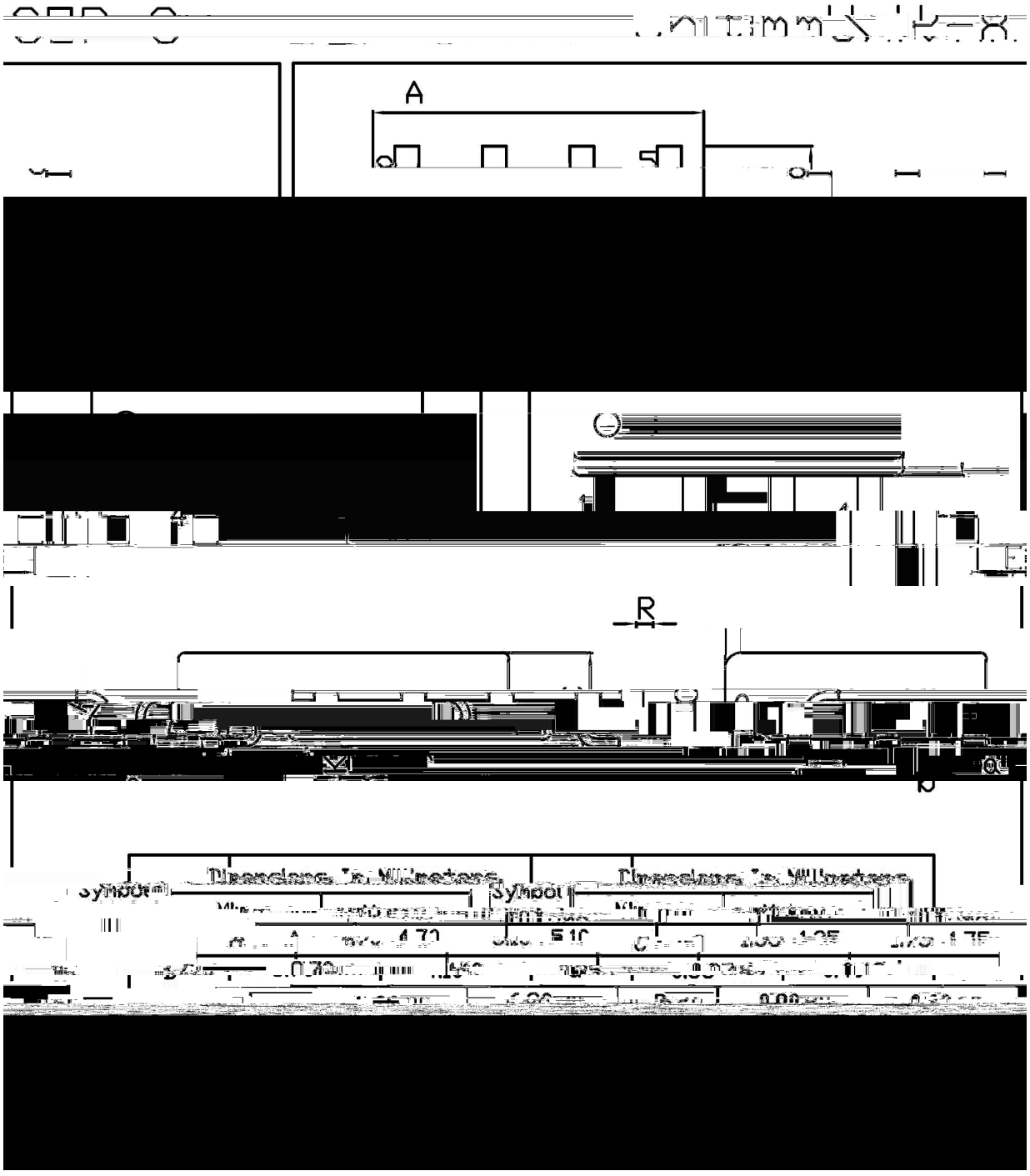
P- / P-CHANNEL Electrical Characteristic Curve



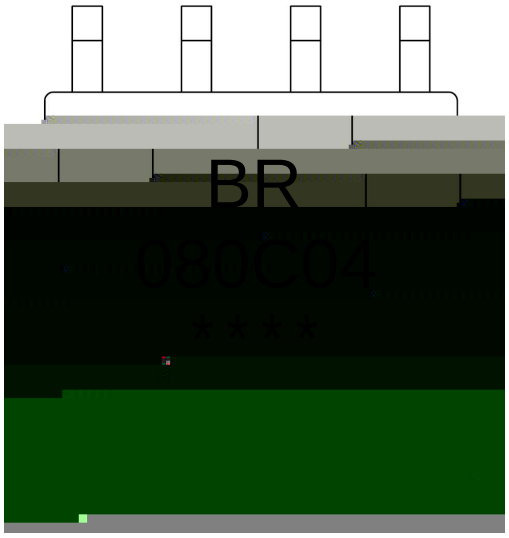




/ Package Dimensions



/ Marking Instructions



BR

080C04

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Note:

BR:	Company Code
080C04:	Product Type
****:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)